

SMD Type

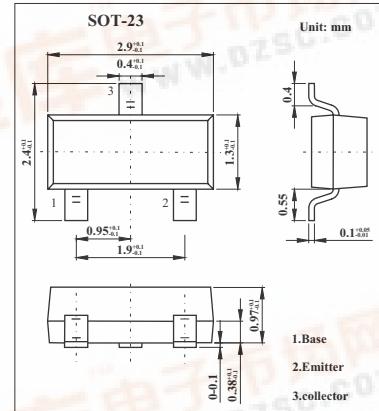
Transistors

High Voltage Transistors

MMBT5550



- Features
- NPN Silicon



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V _{CCEO}	140	V
Collector-base voltage	V _{CBBO}	160	V
Emitter-base voltage	V _{EBO}	6	V
Collector current -continuous	I _C	600	mA
Total device dissipation FR-5 board *1 @TA = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal resistance, junction-to-ambient	R _{θJA}	556	°C/W
Total device dissipation alumina substrate *2 @TA = 25°C derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal resistance, junction-to-ambient	R _{θJA}	417	°C/W
Junction and storage temperature	T _J , T _{stg}	-55 to +150	°C

* 1. FR-5 = 1.0 X 0.75 X 0.062 in.

* 2. Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.

MMBT5550■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter breakdown voltage *	$V_{(\text{BR})\text{CEO}}$	$I_C = 1.0 \text{ mA}, I_B = 0$	140			V
Collector-base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	$I_C = 100 \mu\text{A}, I_E = 0$	160			V
Emitter-base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	$I_E = 10 \mu\text{A}, I_C = 0$	6			V
Collector cutoff current	I_{CBO}	$V_{CB} = 100 \text{ V}, I_E = 0$			100	nA
		$V_{CB} = 100 \text{ V}, I_E = 0, T_a = 100^\circ\text{C}$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 4.0 \text{ V}, I_C = 0$			50	nA
DC current gain	h_{FE}	$I_C = 1.0 \text{ mA}, V_{CE} = 5 \text{ V}$	60			
		$I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	60		250	
		$I_C = 50 \text{ mA}, V_{CE} = 5 \text{ V}$	20			
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$			0.15	V
		$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$			0.25	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$			1.0	V
		$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$			1.2	V
Collector emitter cut-off	I_{CES}	$V_{CB} = 10 \text{ V}$			50	nA
		$V_{CB} = 75 \text{ V}$			100	nA

* Pulse Test: Pulse Width = 300 μs , Duty Cycle=2.0%.

■ Marking

Marking	M1F
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